

<b>SANYO</b>	No.4746	<b>2SJ264</b>
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating easy mounting.

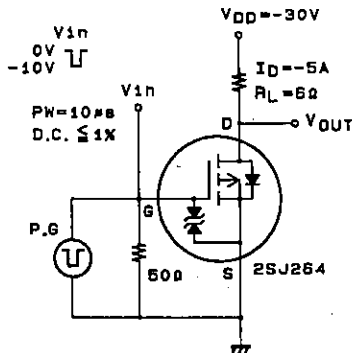
**Absolute Maximum Ratings at Ta = 25°C**

Drain-to-Source Voltage	V <sub>DSS</sub>	-60	V	unit
Gate-to-Source Voltage	V <sub>GSS</sub>	±20	V	
Drain Current(DC)	I <sub>D</sub>	-8	A	
Drain Current(Pulse)	I <sub>DP</sub>	-32	A	
Allowable Power Dissipation	P <sub>D</sub>	2.0	W	
		T <sub>c</sub> = 25°C		
Channel Temperature	T <sub>ch</sub>	25	W	
Storage Temperature	T <sub>stg</sub>	150	°C	
		-55 to +150	°C	

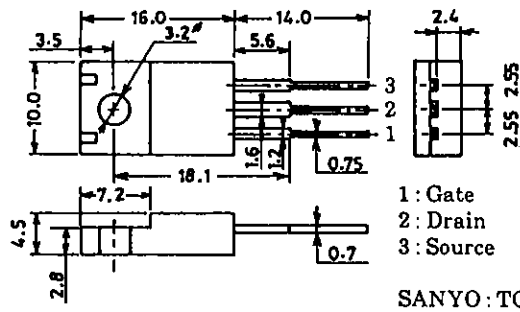
**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1mA, V <sub>GS</sub> = 0	-60			V
G-S Breakdown Voltage	V <sub>(BR)GSS</sub>	I <sub>G</sub> = ±100μA, V <sub>DS</sub> = 0	±20			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -60V, V <sub>GS</sub> = 0			-100	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA	-1.0		-2.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -5A	4	7.5		S
Static Drain-to-Source ON-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = -5A, V <sub>GS</sub> = -10V		0.11	0.15	Ω
	R <sub>DS(on)</sub>	I <sub>D</sub> = -5A, V <sub>GS</sub> = -4V		0.15	0.2	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -20V, f = 1MHz		1230		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -20V, f = 1MHz		390		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = -20V, f = 1MHz		100		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		16		ns
Rise Time	t <sub>r</sub>	"		40		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	"		230		ns
Fall Time	t <sub>f</sub>	"		150		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -8A, V <sub>GS</sub> = 0	-1.0	-1.5		V

**Switching Time Test Circuit**

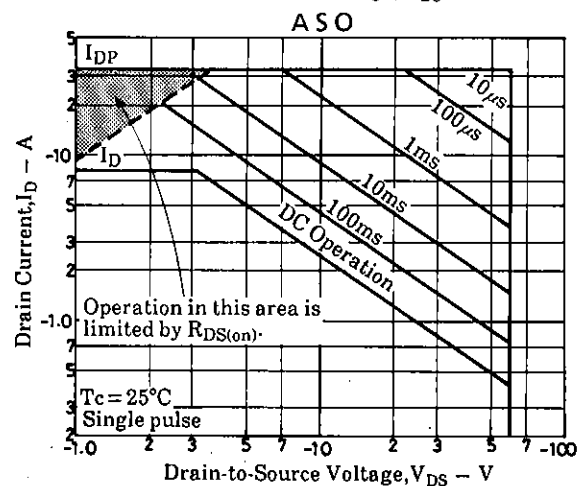
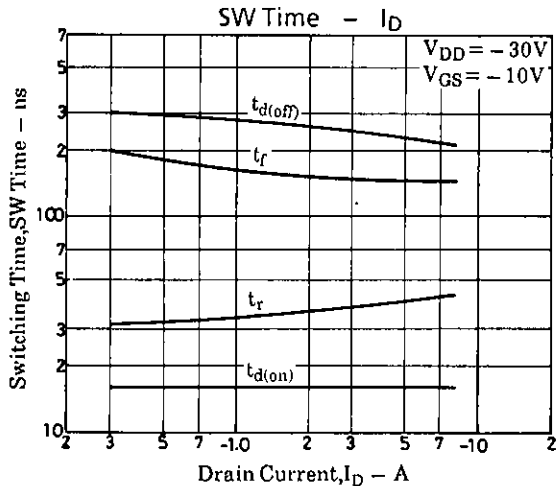
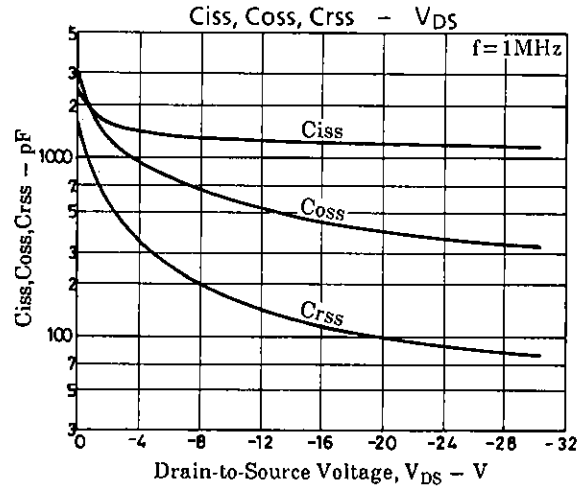
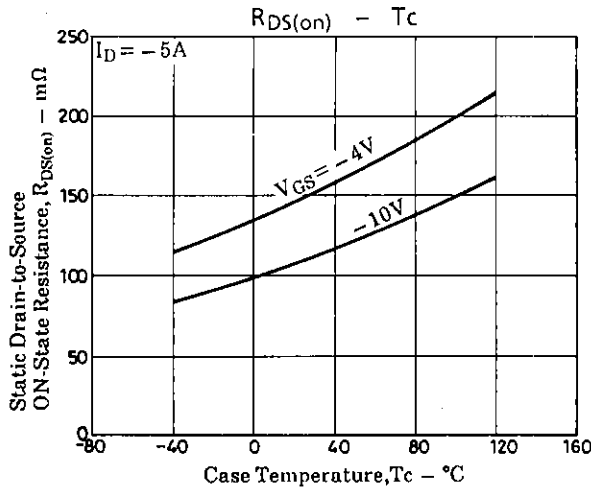
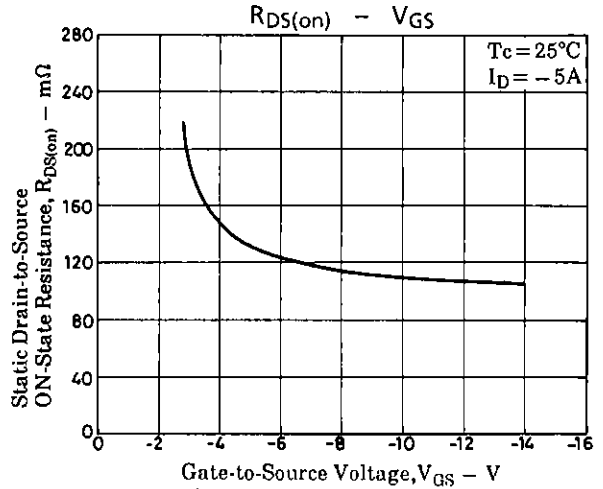
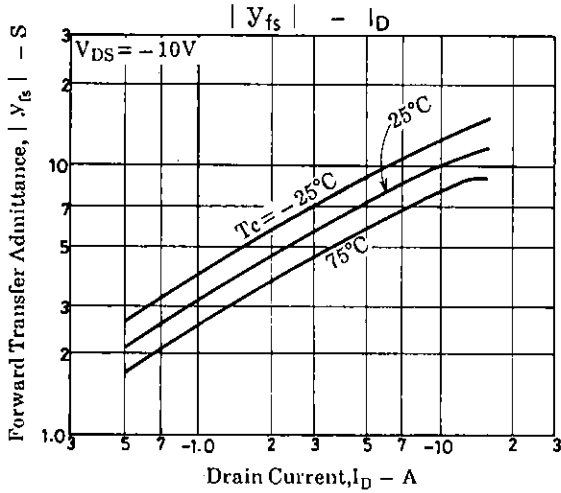
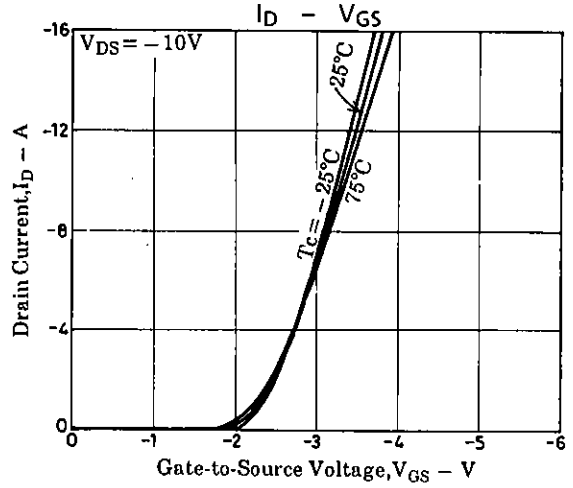
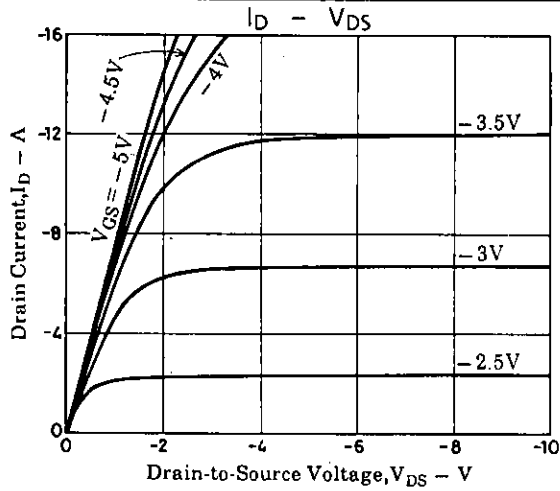


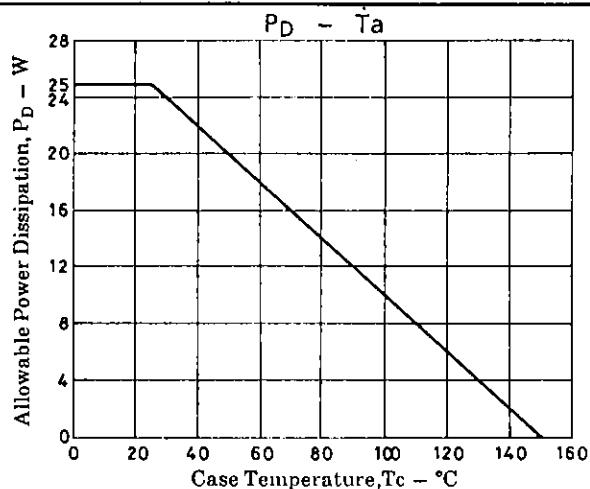
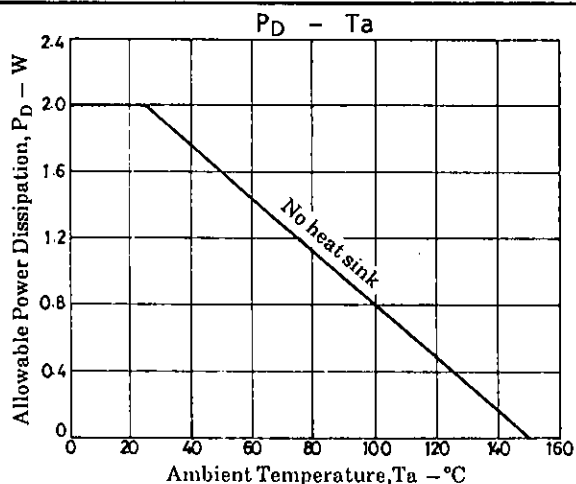
**Package Dimensions 2063A (unit : mm)**



- 1 : Gate
- 2 : Drain
- 3 : Source

SANYO : TO-220ML





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